

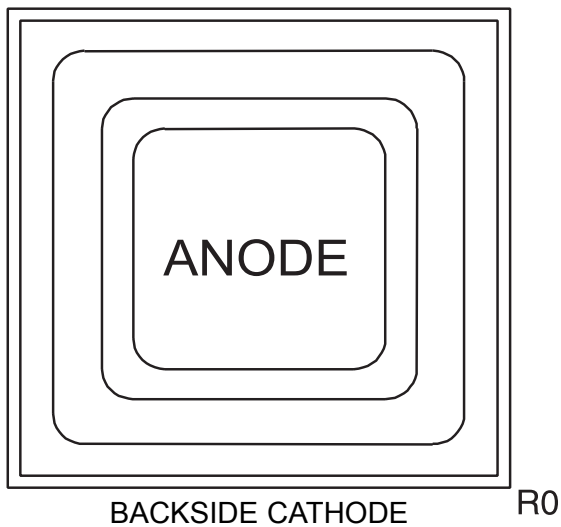
**PROCESS CPD71**  
**Low Leakage Diode**  
Low Leakage Switching Diode Chip

**Central**<sup>TM</sup>  
Semiconductor Corp.

**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	11 MILS
Anode Bonding Pad Area	3.3 x 3.3 MILS
Top Side Metalization	Al - 15,000Å
Back Side Metalization	Au - 18,000Å

**GEOMETRY**



**GROSS DIE PER 4 INCH WAFER**

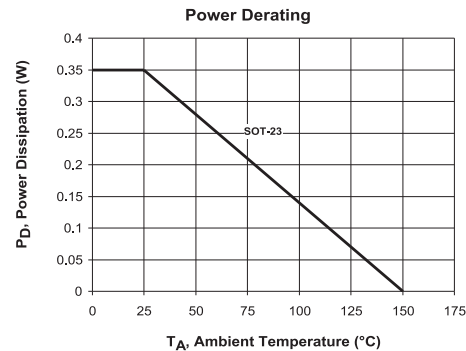
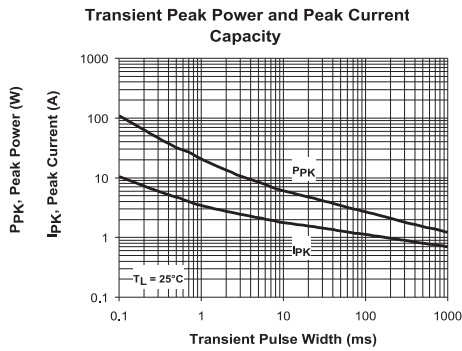
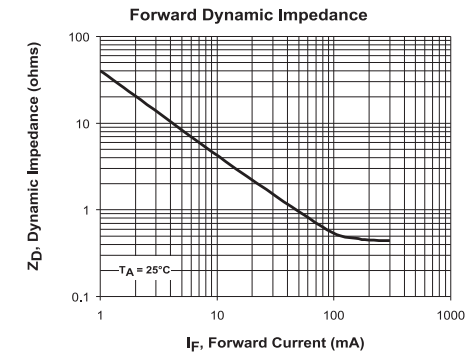
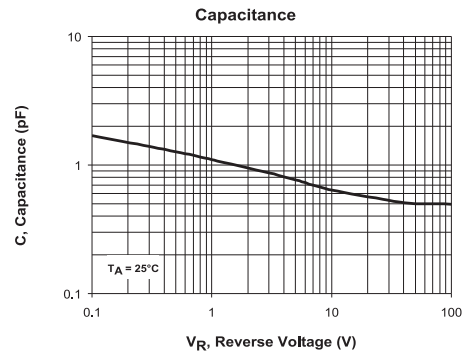
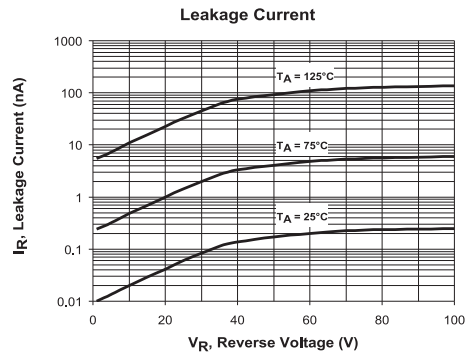
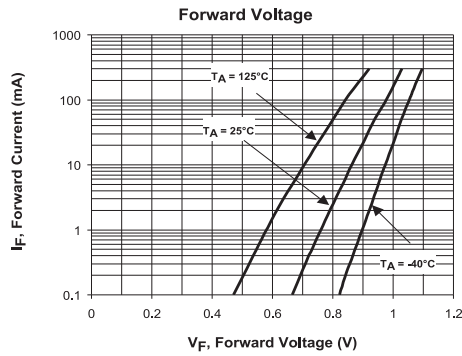
94,130

**PRINCIPAL DEVICE TYPES**

CMPD6001

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R1 (1-August 2002)



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